

ML145407 5 Volt Only Driver/Receiver RS232 EIA-232-E and CCITT V.28

Legacy Device: Motorola MC145407

The ML145407 is a silicon–gate CMOS IC that combines three drivers and three receivers to fulfill the electrical specifications of RS232 EIA–232–E and CCITT V.28 while operating from a single + 5 V power supply. A voltage doubler and inverter convert the + 5V to ± 10 V. This is accomplished through an on–board 20 kHz oscillator and four inexpensive external electrolytic capacitors. The three drivers and three receivers of the ML145407 are virtually identical to those of the ML145406. Therefore, for applications requiring more than three drivers and/or three receivers, an ML145406 can be powered from an ML145407, since the ML145407 charge pumps have been designed to guarantee ± 5 V at the output of up to six drivers. Thus, the ML145407 provides a high–performance, low–power, stand–alone solution or, with the ML145406, a + 5 V only, high–performance two–chip solution.

This device offers the following performance features:

• Operating Temperature Range = $T_A - 40^{\circ}$ to $+85^{\circ}C$

Drivers

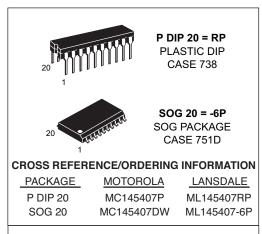
- \pm 7.5 V Output Swing
- 300Ω Power–Off Impedance
- Output Current Limiting
- TTL and CMOS Compatible Inputs
- Slew Rate Range Limited from 4 V/us to 30 V/us

Receivers

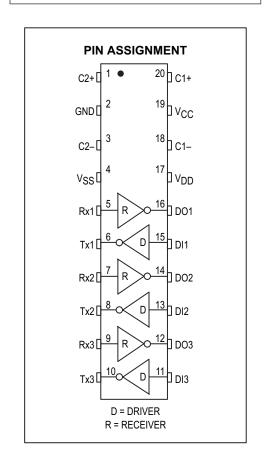
- + 25 V Input Range
- 3 to 7 k Ω Input Impedance
- 0.8 V Hysteresis for Enhanced Noise Immunity

Charge Pumps

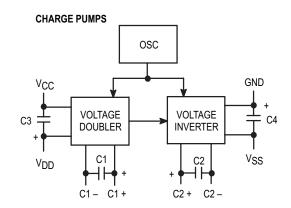
- + 5 V to $\pm 10 \text{ V}$ Dual Charge Pump Architecture
- Supply Outputs Capable of Driving Three On-Chip Drivers and Three Drivers on the ML145406 Simultaneously
- Requires Four Inexpensive Electrolytic Capacitors
- On-Chip 20 kHz Oscillator

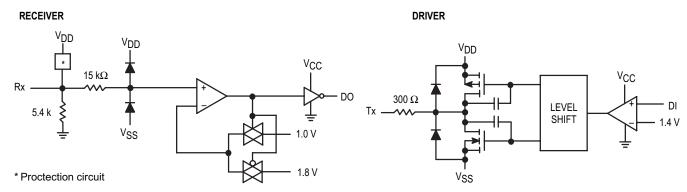


Note: Lansdale lead free (**Pb**) product, as it becomes available, will be identified by a part number prefix change from **ML** to **MLE**.



FUNCTION DIAGRAM





MAXIMUM RATINGS (Voltage polarities referenced to GND)

Rating	Symbol	Value	Unit
DC Supply Voltages	Vcc	- 0.5 to + 6.0	V
Input Voltage Range Rx1 – Rx3 Inputs DI1 – DI3 Inputs	VIR	V _{SS} – 15 to V _{DD} + 15 – 0.5 to (V _{CC} + 0.5)	V
DC Current per Pin	I	± 100	mA
Power Dissipation	PD	1	W
Operating Temperature Range	T _A	– 40 to + 85	°C
Storage Temperature Range	T _{stg}	– 85 to + 150	°C

This device contains protection circuitry to protect the inputs against damage due to high static voltages or electric fields; however, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit. For proper operation, it is recommended that the voltages at the DI and DO pins be constrained to the range GND \leq V $_{DI}$ \leq V $_{CC}$ and GND \leq V $_{DO}$ \leq V $_{CC}$. Also, the voltage at the Rx pin should be constrained to (V $_{SS}$ - 15 V) \leq VRx1 - Rx3 \leq (VDD + 15 V), and Tx should be constrained to V $_{SS}$ \leq VTx1 - Tx3 \leq VDD.

Unused inputs must always be tied to appropriate logic voltage level (e.g., GND or V_{CC} for DI, and GND for Rx).

DC ELECTRICAL CHARACTERISTICS (All polarities referenced to GND = 0 V; C1, C2, C3, C4 = 10 μ F; $T_A = -40$ to + 85°C)

Parameter	Symbol	Min	Тур	Max	Unit
DC Supply Voltage	VCC	4.5	5	5.5	V
Quiescent Supply Current (Outputs unloaded, inputs low)	lcc	_	1.2	3.0	mA
Output Voltage I _{load} = 0 mA I _{load} = 5 mA I _{load} = 10 mA		8.5 7.5 6	10 9.5 9	11 — —	V
I _{load} = 0 mA I _{load} = 5 mA I _{load} = 10 mA	V _{SS}	- 8.5 - 7.5 - 6	- 10 - 9.2 - 8.6	–11 — —	

RECEIVER ELECTRICAL SPECIFICATIONS

(Voltage polarities referenced to GND = 0 V; V_{CC} = + 5 V \pm 10%; C1, C2, C3, C4 = 10 μ F; T_{A} = - 40 to + 85°C)

Characteristic		Symbol	Min	Тур	Max	Unit
Input Turn-on Threshold VDO1 – DO3 = VOL	Rx1 – Rx3	V _{on}	1.35	1.8	2.35	V
Input Turn-off Threshold VDO1 – DO3 = VOH	Rx1 – Rx3	V _{off}	0.75	1.0	1.25	V
Input Threshold Hysteresis (Von – Voff)	Rx1 – Rx3	V _{hys}	0.6	0.8	_	V
Input Resistance	Rx1 – Rx3	R _{in}	3.0	5.4	7.0	kΩ
High–Level Output Voltage VRx1 – Rx3 = -3 V to – 25 V IOH = -20 μA IOH = -1 mA	DO1 – DO3	VOH	V _{CC} - 0.1 V _{CC} - 0.7	 4.3		V
Low-Level Output Voltage VRx1 - Rx3 = + 3 V to + 25 V IOL = + 20 μA IOL = + 1.6 mA	DO1 – DO3	V _{OL}		0.01 0.5	0.1 0.7	V

DRIVER ELECTRICAL SPECIFICATIONS

(Voltage polarities referenced to GND = 0 V: V_{CC} = +5 V \pm 10%; C1, C2, C3, C4 = 10 μ F; T_{A} = -40 to +85°C)

Characteristic			Min	Тур	Max	Unit
Digital Input Voltage Logic 0 Logic 1	DI1 – DI3	V _{IL} VIH	_ 2.0		0.8	V
Input Current GND ≤ V _{DI1} – DI3 ≤ V _{CC}	DI1 – DI3	l _{in}	_	_	± 1.0	μΑ
Output High Voltage V _{DI1} _{– DI3} = Logic 0, R _L = 3.0 kΩ	Tx1 – Tx3 Tx1 – Tx6*	Vон	6 5	7.5 6.5	_	V
Output Low Voltage V _{DI1} – _{DI3} = Logic 1, R _L = 3.0 kΩ	Tx1 – Tx3 Tx1 – Tx6*	VOL	- 6 - 5	- 7.5 - 6.5	_	V
Off Source Impedance (Figure 1)	Tx1 – Tx3	Z _{off}	300	_	_	Ω
Output Short–Circuit Current VCC = + 5.5 V	$ Tx1 - Tx3 \\ Tx1 - Tx3 \text{ shorted to GND**} \\ Tx1 - Tx3 \text{ shorted to } \pm 15 \text{ V***} \\ $	ISC		_	± 60 ± 100	mA

^{*} Specifications for an ML145407 powering an ML145406 with three additional drivers/receivers.

SWITCHING CHARACTERISTICS (V_{CC} = + 5 V \pm 10%; C1, C2, C3, C4 = 10 μ F; T_A = - 40 to + 85°C; See Figures 2 and 3)

Characteristic	Symbo	l Min	Тур	Max	Unit
Drivers	•				
Propagation Delay Time Tx1 – Low–to–High	Tx3 tpLH				μѕ
$R_L = 3 \text{ k}\Omega$, $C_L = 50 \text{ pF or } 2500 \text{ pF}$		_	0.5	1	
High–to–Low R _L = 3 kΩ, C _L = 50 pF or 2500 pF	^t PHL	_	0.5	1	
Output Slew Rate $Tx1 - Minimum Load: R_L = 7 k\Omega, C_L = 0 pF$	Tx3 SR	_	9.0	± 30	V/μs
Maximum Load: R_L = 3 kΩ, C_L = 2500 pF		4.0	T -	_	1
Receivers (C _L = 50 pF)	•		•		
Propagation Delay Time DO1 – I	003				μs
Low-to-High	t _{PLH}	-	-	1	
High-to-Low	t _{PHL}	_	<u> </u>	1	1
Output Rise Time DO1 – I	OO3 t _r	_	250	400	ns
Output Fall Time DO1 – I	OO3 t _f	_	40	100	ns

^{**} Specification is for one Tx output pin to be shorted at a time. Should all three driver outputs be shorted simultaneously, device power dissipation limits could be exceeded.

^{***} This condition could exceed package limitations.

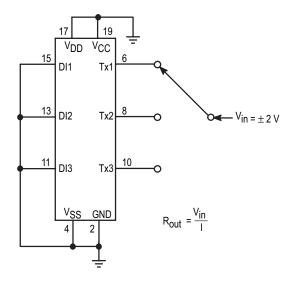
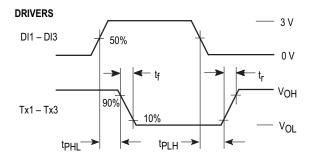


Figure 1. Power-Off Source Resistance



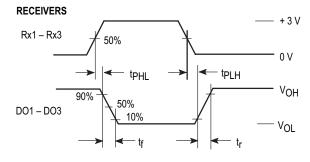


Figure 2. Switching Characteristics

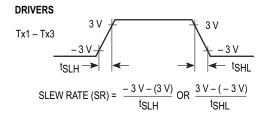


Figure 3. Slew Rate Characterization

PIN DESCRIPTIONS

VCC Digital Power Supply (Pin 19)

The digital supply pin, which is connected to the logic power supply. This pin should have a $0.33~\mu F$ capacitor to ground.

GND

Ground (Pin 2)

Ground return pin is typically connected to the signal ground pin of the EIA–232–E connector (Pin 7) as well as to the logic power supply ground.

V_{DD} Positive Power Supply (Pin 17)

This is the positive output of the on—chip voltage doubler and the positive power supply input of the driver/receiver sections of the device. This pin requires an external storage capacitor to filter the 50% duty cycle voltage generated by the charge pump.

V_{SS} Negative Power Supply (Pin 4)

This is the negative output of the on—chip voltage doubler/inverter and the negative power supply input of the driver/receiver sections of the device. This pin requires an external storage capacitor to filter the 50% duty cycle voltage generated by the charge pump.

These are the connections to the internal voltage doubler and inverter, which generate the VDD and VSS voltages.

Rx1, Rx2, Rx3 Receive Data Input (Pins 5, 7, 9)

These are the EIA–232–E receive signal inputs. A voltage between + 3 and + 25 V is decoded as a space and causes the corresponding DO pin to swing to ground (0 V). A voltage between - 3 and - 25 V is decoded as a mark, and causes the DO pin to swing up to VCC.

DO1, DO2, DO3 Data Output (Pins 16, 14, 12)

These are the receiver digital output pins, which swing from V_{CC} to GND. Each output pin is capable of driving one LSTTL input load.

DI1, DI2, DI3 Data Input (Pins 15, 13, 11)

These are the high impedance digital input pins to the drivers. Input voltage levels on these pins must be between $V_{\rm CC}$ and GND.

Tx1, Tx2, Tx3 Transmit Data Output (Pins 6, 8, 10)

These are the EIA–232–E transmit signal output pins,which swing toward V_{DD} and V_{SS} . A logic 1 at a DI input causes the corresponding Tx output to swing toward V_{SS} . A logic 0 causes the output to swing toward V_{DD} . The actual levels and slew rate achieved will depend on the output loading (RL\\CL).

ESD CONSIDERATIONS

ESD protection on IC devices that have their pins accessible to the outside world is essential. High static voltages applied to the pins when someone touches them either directly or indirectly can cause damage to gate oxides and transistor junctions by coupling a portion of the energy from the I/O pin to the power supply busses of the IC. This coupling will usually occur through the internal ESD protection diodes. The key to protecting the IC is to shunt as much of the energy to ground as possible before it enters the IC. Figure 7 shows a technique which will clamp the ESD voltage at approximately $\pm 15~V$ using the MMBZ15VDLT1. Any residual voltage which appears on the supply pins is shunted to ground through the $0.1~\mu F$ capacitors.

OPERATION WITH SMALLER VALUE CHARGE PUMP CAPS

The ML145407 is characterized in the electrical tables using

 $10~\mu F$ charge pump caps to illustrate its capability in driving a companion ML145406 or ML145403. If there is no requirement to support a second interface device and/or the charge pump is not being used to power any other components, the ML145407 is capable of complying with EIA–232–E and V.28 with smaller value charge pump caps. Table 1 summarizes driver performance with both 2.2 μF and 1.0μF charge pump caps.

Table 1. Typical Performance

Parameter	2.2 μ F	1.0 μ F
Tx V _{OH} @ 25°C	7.3	7.2
Tx V _{OH} @ 85°C	7.2	7.1
Tx V _{OL} @ 25°C	- 6.5	- 6.4
Tx V _{OL} @ 85°C	- 6.1	- 6.0
Tx Slew Rate @ 25°C	8.0 V/μs	8.0 V/μs
Tx Slew Rate @ 85°C	7.0 V/μs	7.0 V/μs

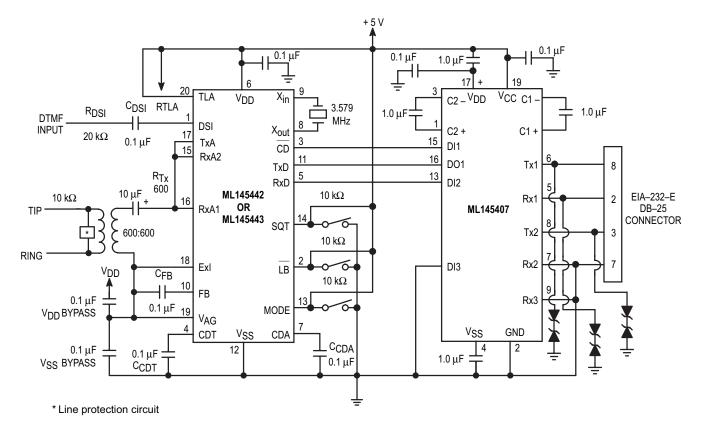


Figure 4. 5 V, 300 Baud Modem with EIA-232-E Interface

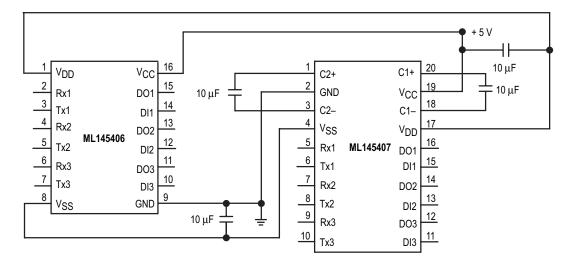


Figure 5. ML145406/ML145407 5 V Only Solution for up to Six EIA-232-E Drivers and Receivers

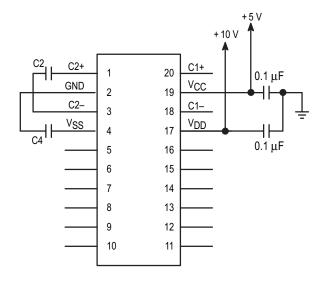


Figure 6. Two Supply Configuration (ML145407 Generates VSS Only)

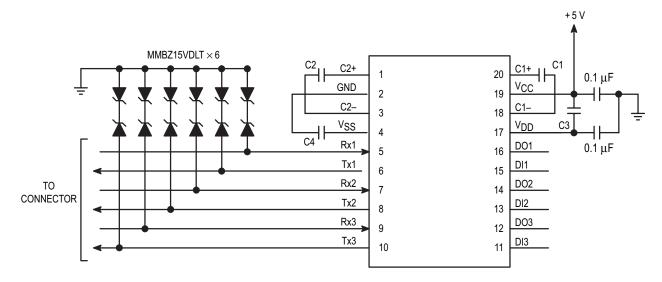
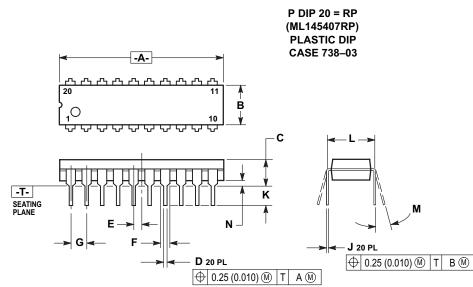


Figure 7. ESD Protection Scheme

OUTLINE DIMENSIONS

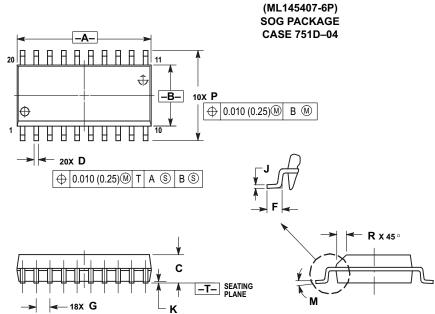
SOG 20 = -6P



NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	ETERS
DIM	MIN	MAX	MIN	MAX
Α	1.010	1.070	25.66	27.17
В	0.240	0.260	6.10	6.60
С	0.150	0.180	3.81	4.57
D	0.015	0.022	0.39	0.55
E	0.050	BSC	1.27	BSC
F	0.050	0.070	1.27	1.77
G	0.100 BSC		2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.140	2.80	3.55
L	0.300	BSC	7.62	BSC
М	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.
- 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.150
- (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 (0.005) TOTAL IN EXCESS OF D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	INC	HES	MILLIN	METERS
DIM	MIN	MAX	MIN	MAX
Α	12.65	12.95	0.499	0.510
В	7.40	7.60	0.292	0.299
С	2.35	2.65	0.093	0.104
D	0.35	0.49	0.014	0.019
F	0.50	0.90	0.020	0.035
G	1.27	BSC	0.050	BSC
J	0.25	0.32	0.010	0.012
K	0.10	0.25	0.004	0.009
M	0 °	7 °	0 °	7 °
Р	10.05	10.55	0.395	0.415
R	0.25	0.75	0.010	0.029

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